













SN74LVC2G157

SCES207M - APRIL 1999-REVISED JUNE 2015

SN74LVC2G157 Single 2-Line to 1-Line Data Selector Multiplexer

Features

- Available in the Texas Instruments NanoFree™ Package
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Max t_{pd} of 6 ns at 3.3 V
- Low Power Consumption, 10-µA Maximum I_{CC}
- ±24-mA Output Drive at 3.3 V
- Typical V_{OLP} (Output Ground Bounce) $<0.8 \text{ V at V}_{CC} = 3.3 \text{ V}, T_A = 25^{\circ}\text{C}$
- Typical V_{OHV} (Output V_{OH} Undershoot) >2 V at V_{CC} = 3.3 V, T_A = 25°C
- Ioff Supports Live Insertion, Partial-Power-Down Mode, and Back-Drive Protection
- Can Be Used as a Down Translator to Translate Inputs From a Maximum of 5.5 V Down to the V_{CC} Level
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human Body Model (A114-A)
 - 1000-V Charged-Device Model (C101)

Applications

- Barcode Scanner
- Cable Solutions
- E-Books
- Embedded PC
- Field Transmitter: Temperature or Pressure Sensors
- Fingerprint Biometrics
- HVAC: Heating, Ventilating, and Air Conditioning
- Network-Attached Storage (NAS)
- Server Motherboard and PSU
- Software Defined Radio (SDR)
- TV: High Definition (HDTV), LCD, and Digital
- Video Communications Systems
- Wireless Data Access Cards, Headsets, Keyboards, Mice, and LAN Cards

3 Description

This single 2-line to 1-line data selector multiplexer is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC2G157 device features a common strobe (G) input. When the strobe is high, Y is low and \overline{Y} is high. When the strobe is low, a single bit is selected from one of two sources and is routed to the outputs. The device provides true and complementary data.

NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

This device is fully specified for partial-power-down applications using Ioff. The Ioff circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
SN74LVC2G157DCT	SSOP (8)	2.95 mm × 2.80 mm
SN74LVC2G157DCU	VSSOP (8)	2.30 mm × 2.00 mm
SN74LVC2G157YZP	DSBGA (8)	1.91 mm × 0.91 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Logic Diagram (Positive Logic)

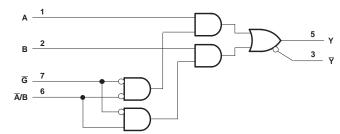




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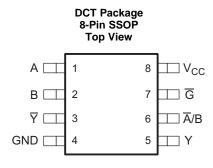
4 Revision History

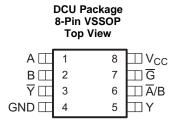
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision L (January 2014) to Revision M	Page
Added ESD Ratings table	4
Added Thermal Information table	5
Added Typical Characteristics	6
Added Mechanical, Packaging, and Orderable Information section	12
Changes from Revision K (January 2007) to Revision L	Page
Updated document to new TI data sheet format	1
Removed Ordering Information table	1



5 Pin Configuration and Functions





YZP Package 8-Pin DSBGA Bottom View

See mechanical drawings for dimensions

Pin Functions

	PIN						
NAME	SSOP, VSSOP	DSBGA	I/O	DESCRIPTION			
Α	1	1	I	Data Input			
Ā/B	6	6	I	Input Selector			
В	2	2	Ι	Data Input			
G	7	7	I	Common Strobe Input			
GND	4	4	_	Ground			
V _{CC}	8	8		Power			
Υ	5	5	0	Output			
7	3	3	0	Inverted Output			



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		-0.5	6.5	V
V_{I}	Input voltage ⁽²⁾		-0.5	6.5	V
V_{O}	Voltage applied to any output in the high-impedance or power-off state (2)		-0.5	6.5	V
Vo	Voltage applied to any output in the high or low state (2)(3)		-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		-50	mA
I _{OK}	Output clamp current	V _O < 0		-50	mA
Io	Continuous output current			±50	mA
	Continuous current through V _{CC} or GND			±100	mA
T _{stg}	Storage temperature		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
, Electrostatic	Electrostatic	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	2000	V
V _(ESD)	discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	1000	٧

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

See (1).

			MIN	MAX	UNIT	
.,	Complements	Operating	1.65	5.5	V	
V _{CC}	Supply voltage	Data retention only	1.5		V	
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}			
V	High level input voltage	V _{CC} = 2.3 V to 2.7 V	1.7		V	
V _{IH}	High-level input voltage	V _{CC} = 3 V to 3.6 V	2		V	
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}			
	Low-level input voltage	V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}		
.,		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V	
V_{IL}		Low-level input voltage	Low-level input voltage	V _{CC} = 3 V to 3.6 V		0.8
		V _{CC} = 4.5 V to 5.5 V		0.3 × V _{CC}		
V_{I}	Input voltage		0	5.5	V	
Vo	Output voltage		0	V _{CC}	V	
		V _{CC} = 1.65 V		-4		
		V _{CC} = 2.3 V		-8		
I _{OH}	High-level output current	V 2.V		-16	mA	
		V _{CC} = 3 V		-24		
		V _{CC} = 4.5 V		-32		

 All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, SCBA004.

⁽²⁾ The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

⁽³⁾ The value of V_{CC} is provided in the *Recommended Operating Conditions* table.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



Recommended Operating Conditions (continued)

See (1).

			MIN	MAX	UNIT
		V _{CC} = 1.65 V		4	
I _{OL}	V _{CC} = 2.3 V	V _{CC} = 2.3 V		8	
	Low-level output current	Low-level output current		16	mA
		V _{CC} = 3 V		24	
		V _{CC} = 4.5 V		32	
		$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}, 2.5 \text{ V} \pm 0.2 \text{ V}$		20	
Δt/Δν	Input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	ns/V
		$V_{CC} = 5 V \pm 0.5 V$		5	
T _A	Operating free-air temperature		-40	85	°C

6.4 Thermal Information

	THERMAL METRIC ⁽¹⁾	DCT (SSOP)	DCU (VSSOP)	YZP (DSBGA)	UNIT
		8 PINS	8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	220	227	102	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

Р	ARAMETER	TEST CONDITIONS		V _{CC}	MIN	TYP ⁽¹⁾	MAX	UNIT
		$I_{OH} = -100 \mu A$		5 V to 5.5 V	$V_{CC} - 0.1$			
		$I_{OH} = -4 \text{ mA}$		1.65 V	1.2			
.,		$I_{OH} = -8 \text{ mA}$		2.3 V	1.9			V
V _{OH}		$I_{OH} = -16 \text{ mA}$		3 V	2.4			V
		$I_{OH} = -24 \text{ mA}$		3 V	2.3			
	$I_{OH} = -32 \text{ mA}$		4.5 V	3.8				
		I _{OL} = 100 μA	1.6	5 V to 5.5 V			0.1	
		$I_{OL} = 4 \text{ mA}$		1.65 V		(0.45	
\/		$I_{OL} = 8 \text{ mA}$		2.3 V			0.3	V
V _{OL}		I _{OL} = 16 mA		3 V			0.4	'
		$I_{OL} = 24 \text{ mA}$		3 V		(0.55	
		I _{OL} = 32 mA		4.5 V		(0.55	
II	A, B, or control inputs	$V_I = 5.5 \text{ V or GND}$	C	0 to 5.5 V			±5	μΑ
I _{off}		V_I or $V_O = 5.5 \text{ V}$		0			±10	μΑ
I_{CC}		$V_I = 5.5 \text{ V or GND}, \qquad \qquad I_O = 0$	1.6	5 V to 5.5 V			10	μΑ
ΔI _{CC}	>	One input at $V_{CC} - 0.6 \text{ V}$, Other input	s at V _{CC} or GND 3	V to 5.5 V			500	μΑ
C_{i}		$V_I = V_{CC}$ or GND		3.3 V		5		pF

(1) All typical values are at V_{CC} = 3.3 V, T_A = 25°C.



6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1 ± 0.1	1.8 V 5 V	V _{CC} = 2 ± 0.2		V _{CC} = ± 0.3		V _{CC} = ± 0.5	5 V 5 V	UNIT
	(INPOT)	(001F01)		MAX	MIN	MAX	MIN	MAX	MIN	MAX	
	A or B		4.4	14	2.1	8	2	6	1.4	4	
t_{pd}	Ā/B	Y or \overline{Y}	4.9	16	2.5	9	2.1	6	1.6	4	ns
	G		4.2	14	2	8	1.6	6	1.3	4	

6.7 Operating Characteristics

 $T_A = 25^{\circ}C$

	PARAMETER	TEST CONDITIONS	V _{CC} = 1.8 V	$V_{CC} = 2.5 \text{ V}$	$V_{CC} = 3.3 \text{ V}$	$V_{CC} = 5 V$	UNIT
	PARAMETER	TEST CONDITIONS	TYP	TYP	TYP	TYP	ONII
C_{pd}	Power dissipation capacitance	f = 10 MHz	35	35	37	40	pF

6.8 Typical Characteristics

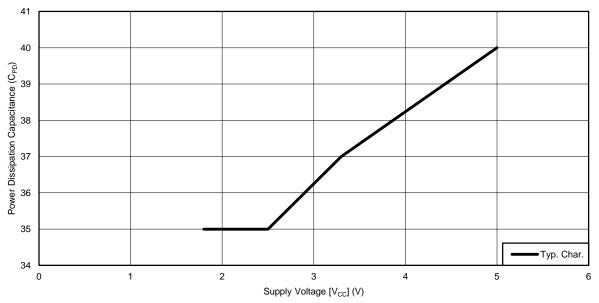


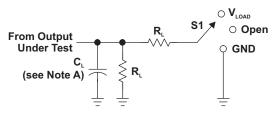
Figure 1. Voltage vs Capacitance

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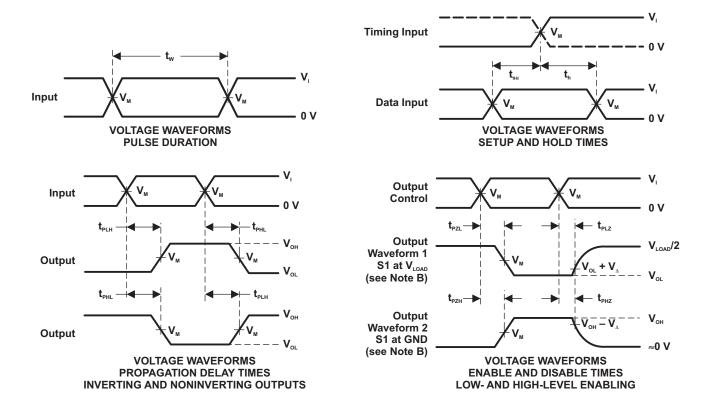
7 Parameter Measurement Information



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	\mathbf{V}_{LOAD}
t _{PHZ} /t _{PZH}	GND

100	\mathbf{r}	\mathbf{n}	шт
LOA	\mathbf{D}	IKC	UII

.,	INI	PUTS		V		-	V	
V _{cc}	V _{cc} V _i		V _M	V _{LOAD}	C _L	$R_{\scriptscriptstyle L}$	V _A	
1.8 V ± 0.15 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	1 k Ω	0.15 V	
2.5 V ± 0.2 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	500 Ω	0.15 V	
$3.3 \text{ V} \pm 0.3 \text{ V}$	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V	
5 V ± 0.5 V	V _{cc}	≤2.5 ns	V _{cc} /2	2 × V _{cc}	50 pF	500 Ω	0.3 V	



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_{\circ} = 50 Ω .
- D. The outputs are measured one at a time, with one transition per measurement.
- E. $t_{\mbox{\tiny PLZ}}$ and $t_{\mbox{\tiny PHZ}}$ are the same as $t_{\mbox{\tiny dis}}.$
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 2. Load Circuit and Voltage Waveforms



8 Detailed Description

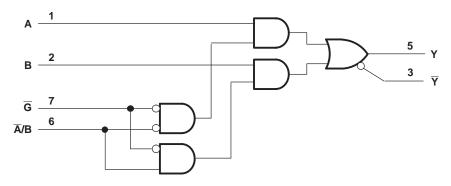
8.1 Overview

This single 2-line to 1-line data selector multiplexer is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC2G157 device features a common strobe (\overline{G}) input. When the strobe is high, Y is low and \overline{Y} is high. When the strobe is low, a single bit is selected from one of two sources and is routed to the outputs. The device provides true and complementary data.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

8.2 Functional Block Diagram



8.3 Feature Description

The SN74LVC2G157 device has a wide operating V_{CC} range of 1.65 V to 5.5 V, which allows it to be used in a broad range of systems. The 5.5 V I/Os allow down translation and also allow voltages at the inputs when $V_{CC} = 0$

8.4 Device Functional Modes

Table 1 lists the functional modes for SN74LVC2G157.

Table 1. Function Table

	INP	OUTI	PUTS		
G	A/B	Α	В	Y	Y
Н	Х	Х	Χ	L	Н
L	L	L	Χ	L	Н
L	L	Н	Χ	Н	L
L	Н	Х	L	L	Н
L	Н	Х	Н	Н	L

Product Folder Links: SN74LVC2G157



9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The LVC family is Tl's premier solution to the industry's high-drive needs in logic devices. The LVC family ensures a symmetric drive of 24 mA across the range 3.3 V < V_{CC} < 5.5 V. The SN74LVC2G157 device also maintains excellent response time. The increased drive produces faster edges and improved response performance.

9.2 Typical Application

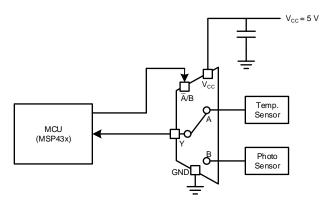


Figure 3. Multiplexer Controlled by Processor

9.2.1 Design Requirements

The SN74LVC2G157 device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits.

The SN74LVC2G157 allows switching control of analog and digital signals with a digital control signal. All input signals should remain as close to either 0 V or V_{CC} for optimal operation.

9.2.2 Detailed Design Procedure

- 1. Recommended input conditions:
 - For rise time and fall time specifications, see $\Delta t/\Delta v$ in the table.
 - For specified high and low levels, see V_{IH} and V_{IL} in the table.
 - Inputs and outputs are overvoltage tolerant and can therefore go as high as 5.5 V at any valid V_{CC}.
- 2. Recommended output conditions:
 - Load currents should not exceed ±50 mA.
- 3. Frequency selection criterion:
 - The effects of frequency upon the output current should be studied in Figure 5.
 - Added trace resistance and capacitance can reduce maximum frequency capability; follow the layout practices listed in the Layout section.

Typical Application (continued)

9.2.3 Application Curve

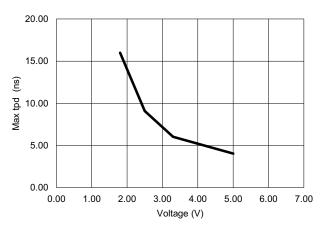


Figure 4. Max tpd vs Voltage of LVC Family

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the table

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- μ F bypass capacitor is recommended. If multiple pins are labeled V_{CC} , then a 0.01- μ F or 0.022- μ F capacitor is recommended for each V_{CC} because the V_{CC} pins are tied together internally. For devices with dual supply pins operating at different voltages, for example V_{CC} and V_{DD} , a 0.1- μ F bypass capacitor is recommended for each supply pin. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of 0.1 μ F and 1 μ F are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

11 Layout

11.1 Layout Guidelines

Reflections and matching are closely related to the loop antenna theory but are different enough to be discussed separately from the theory. When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self–inductance of the trace which results in the reflection. Not all PCB traces can be straight and therefore some traces must turn corners. Figure 5 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.



11.2 Layout Example

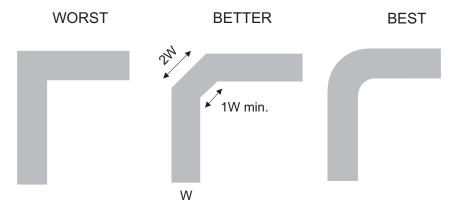


Figure 5. Trace Example



12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

- Implications of Slow or Floating CMOS Inputs, SCBA004
- Selecting the Right Texas Instruments Signal Switch, SZZA030

12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community T's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.3 Trademarks

NanoFree, E2E are trademarks of Texas Instruments. All other trademarks are the property of their respective owners.

12.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.





26-Sep-2015

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
74LVC2G157DCTRE4	ACTIVE	SM8	DCT	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	C57 Z	Samples
74LVC2G157DCURE4	ACTIVE	VSSOP	DCU	8		TBD	Call TI	Call TI	-40 to 85		Samples
74LVC2G157DCURG4	ACTIVE	VSSOP	DCU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	C57R	Samples
74LVC2G157DCUTE4	ACTIVE	VSSOP	DCU	8		TBD	Call TI	Call TI	-40 to 85		Samples
74LVC2G157DCUTG4	ACTIVE	VSSOP	DCU	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	C57R	Samples
SN74LVC2G157DCTR	ACTIVE	SM8	DCT	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	C57 Z	Samples
SN74LVC2G157DCTRG4	ACTIVE	SM8	DCT	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	C57 Z	Samples
SN74LVC2G157DCUR	ACTIVE	VSSOP	DCU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	Level-1-260C-UNLIM	-40 to 85	(C57Q ~ C57R)	Samples
SN74LVC2G157DCUT	ACTIVE	VSSOP	DCU	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU CU SN	Level-1-260C-UNLIM	-40 to 85	(C57Q ~ C57R)	Samples
SN74LVC2G157YZPR	ACTIVE	DSBGA	YZP	8	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(C37 ~ C3N)	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.



PACKAGE OPTION ADDENDUM

26-Sep-2015

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

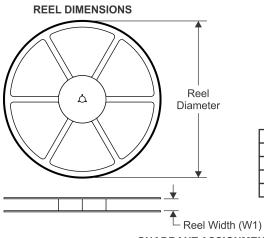
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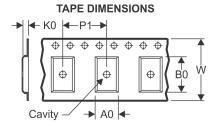
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PACKAGE MATERIALS INFORMATION

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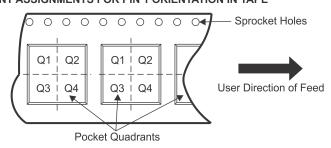
TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

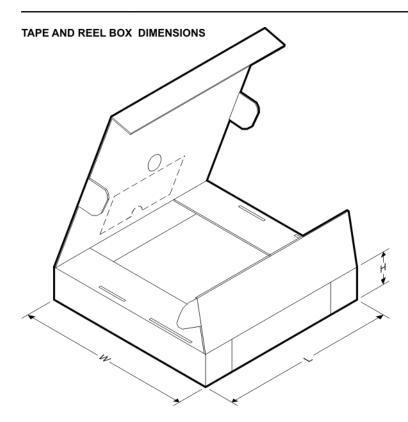


*All dimensions are nominal

All differsions are nothinal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74LVC2G157DCURG4	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
74LVC2G157DCUTG4	VSSOP	DCU	8	250	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G157DCTR	SM8	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
SN74LVC2G157DCUR	VSSOP	DCU	8	3000	178.0	9.5	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G157DCUR	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G157DCUT	VSSOP	DCU	8	250	178.0	9.5	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G157YZPR	DSBGA	YZP	8	3000	178.0	9.2	1.02	2.02	0.63	4.0	8.0	Q1

PACKAGE MATERIALS INFORMATION

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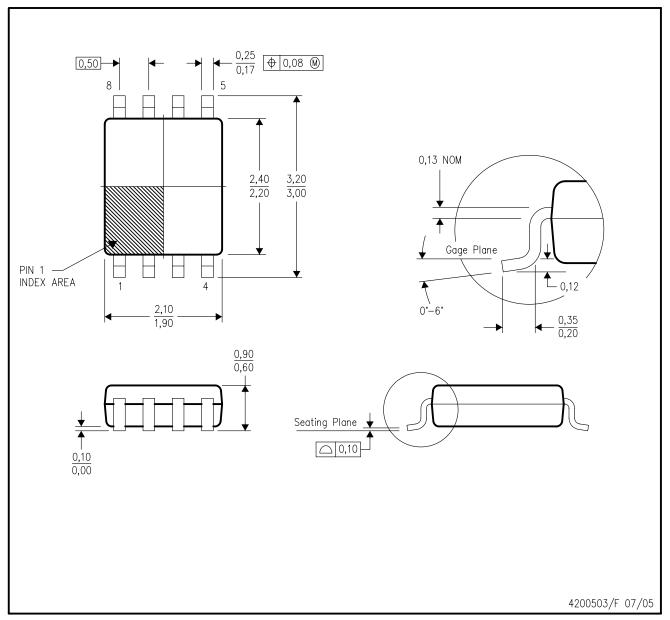


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74LVC2G157DCURG4	VSSOP	DCU	8	3000	202.0	201.0	28.0
74LVC2G157DCUTG4	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74LVC2G157DCTR	SM8	DCT	8	3000	182.0	182.0	20.0
SN74LVC2G157DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74LVC2G157DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74LVC2G157DCUT	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74LVC2G157YZPR	DSBGA	YZP	8	3000	220.0	220.0	35.0

DCU (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



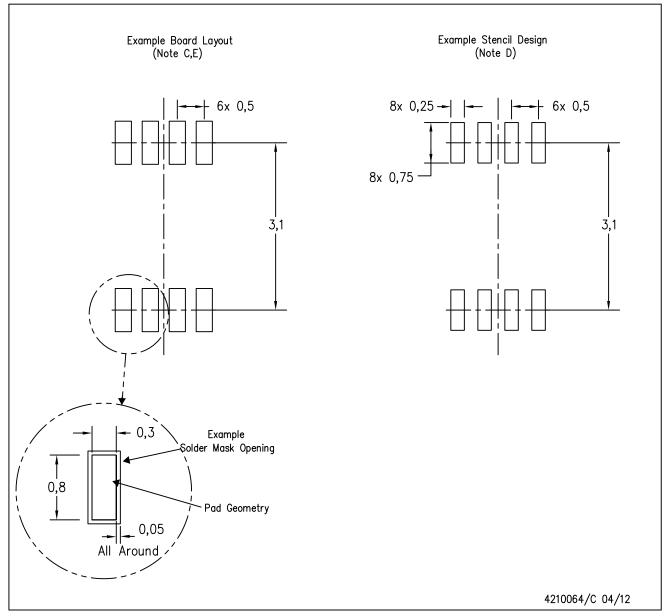
NOTES:

- : A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
 - D. Falls within JEDEC MO-187 variation CA.



DCU (S-PDSO-G8)

PLASTIC SMALL OUTLINE PACKAGE (DIE DOWN)



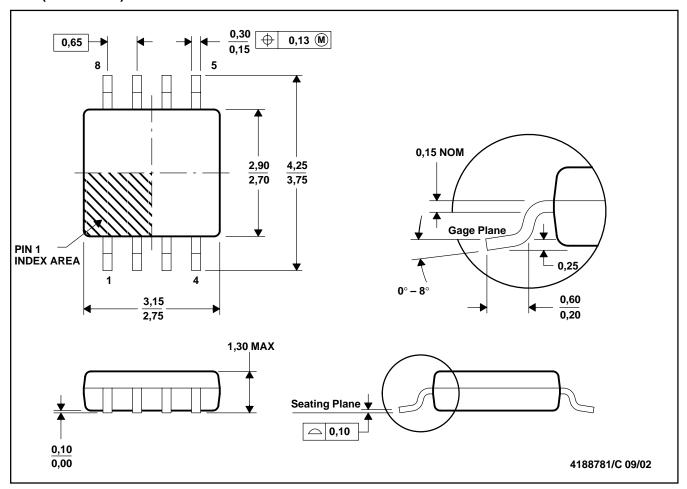
NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



DCT (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE

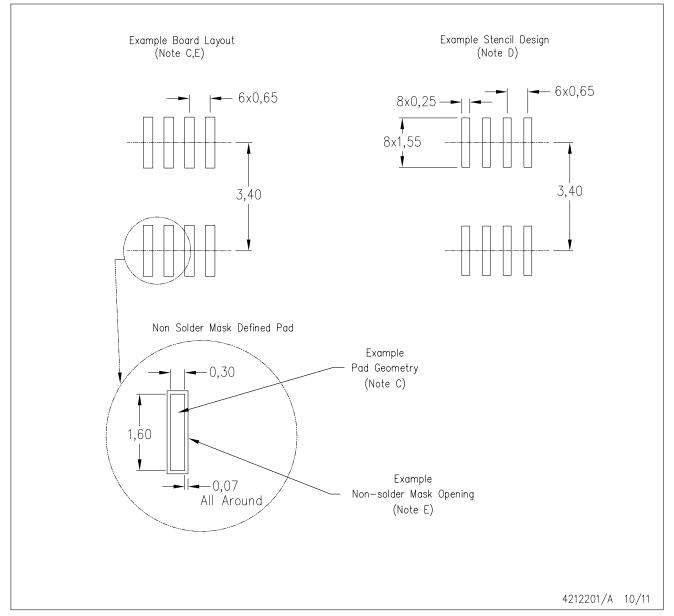


NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion
- D. Falls within JEDEC MO-187 variation DA.

DCT (R-PDSO-G8)

PLASTIC SMALL OUTLINE



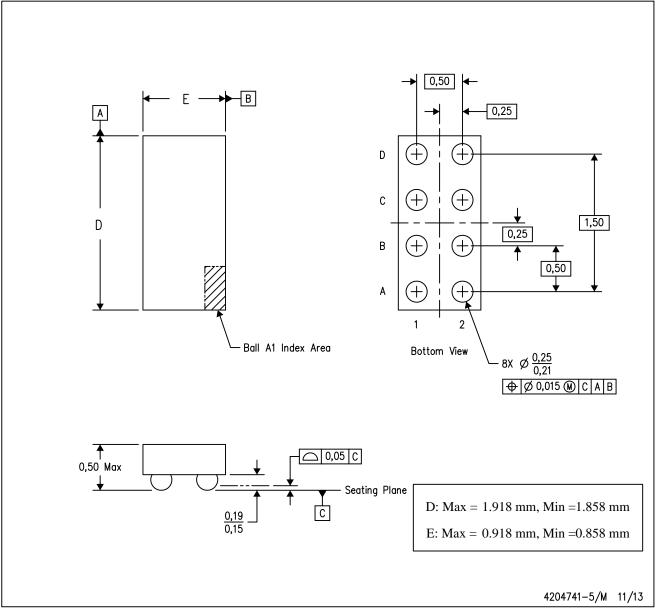
NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



YZP (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

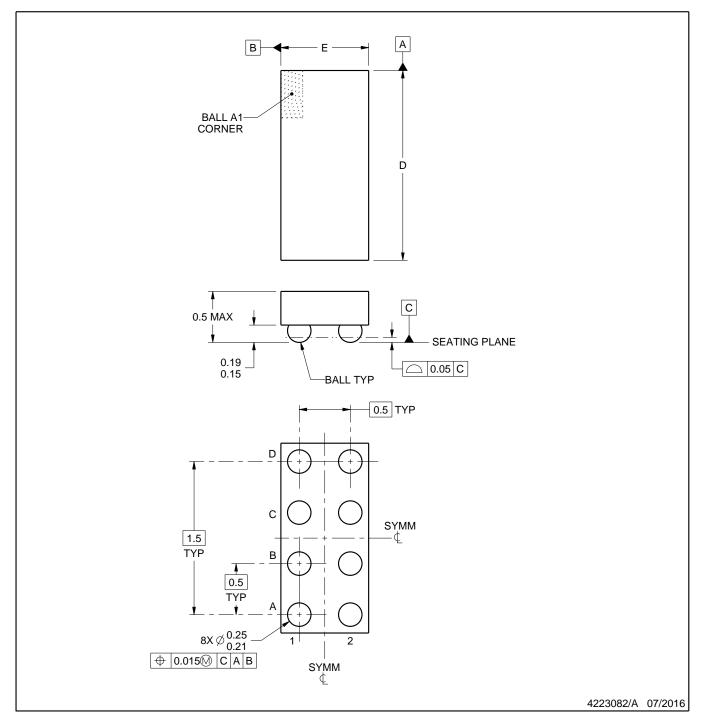
- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.

NanoFree is a trademark of Texas Instruments.





DIE SIZE BALL GRID ARRAY



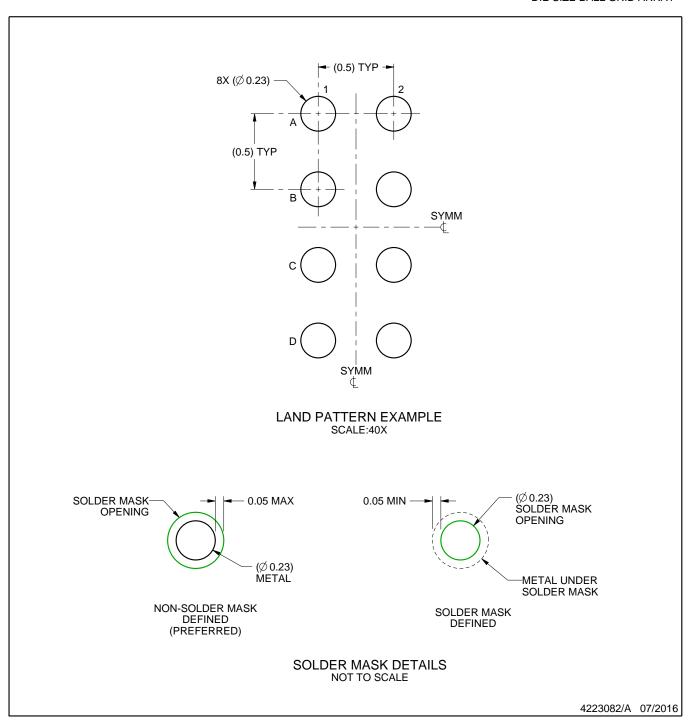
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY

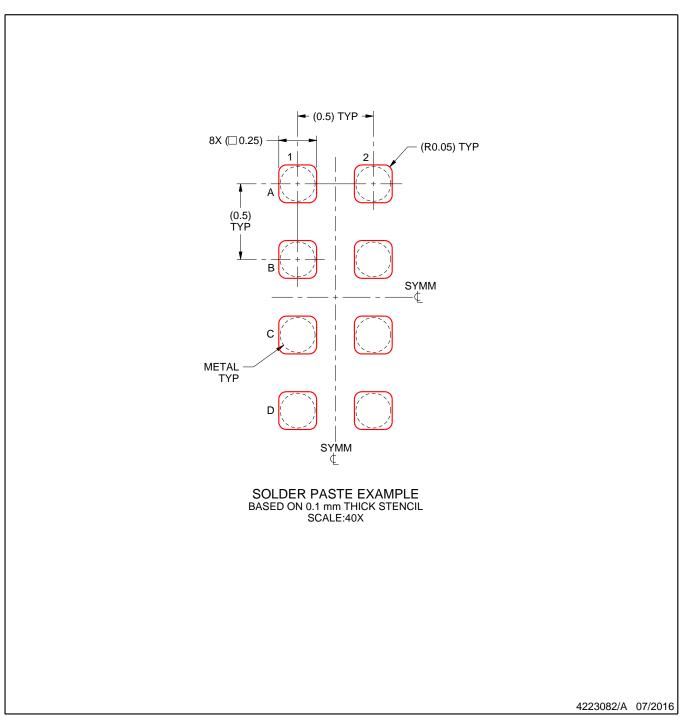


NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



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